

Silicon PNP Power Transistors

2N4901 2N4902 2N4903

DESCRIPTION

- With TO-3 package
- Complement to type 2N5067/5068/5069
- Low collector saturation voltage

APPLICATIONS

- For general-purpose switching and power amplifier applications.

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

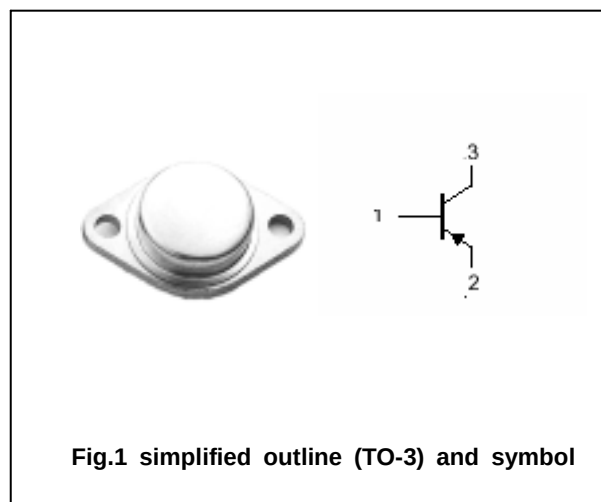


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings($T_a = ^\circ\text{C}$)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2N4901	Open emitter	-40	V
		2N4902		-60	
		2N4903		-80	
V_{CEO}	Collector-emitter voltage	2N4901	Open base	-40	V
		2N4902		-60	
		2N4903		-80	
V_{EBO}	Emitter-base voltage		Open collector	-5	V
I_C	Collector current			-5	A
I_{CM}	Collector current-peak			-10	A
I_B	Base current			-1	A
P_D	Total power dissipation		$T_C = 25^\circ\text{C}$	87.5	W
T_j	Junction temperature			200	$^\circ\text{C}$
T_{stg}	Storage temperature			-65~200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-c}$	Thermal resistance junction to case	2.0	$^\circ\text{C/W}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE0(SUS)}	Collector-emitter sustaining voltage	2N4901	I _C =-0.2A ; I _B =0	-40			V
		2N4902		-60			
		2N4903		-80			
V _{CEsat-1}	Collector-emitter saturation voltage		I _C =-1A; I _B =-0.1A			-0.4	V
V _{CEsat-2}	Collector-emitter saturation voltage		I _C =-5A ; I _B =-1A			-1.5	V
V _{BE}	Base-emitter on voltage		I _C =-1A ; V _{CE} =-2V			-1.2	V
I _{CEO}	Collector cut-off current		V _{CE} =Rated V _{CE0} ; I _B =0			-1.0	mA
I _{CBO}	Collector cut-off current		V _{CB} =Rated V _{CBO} ; I _E =0			-0.1	mA
I _{CEX}	Collector cut-off current		V _{CE} = Rated V _{CE0} ; V _{BE(off)} =1.5V T _C =150°C			-1.0 -2.0	mA
I _{EBO}	Emitter cut-off current		V _{EB} =-5V; I _C =0			-1.0	mA
h _{FE-1}	DC current gain		I _C =-1A ; V _{CE} =-2V	20		80	
h _{FE-2}	DC current gain		I _C =-5A ; V _{CE} =-2V	7			
f _T	Transition frequency		I _C =-1A ; V _{CE} =-10V	4			MHz

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PACKAGE OUTLINE

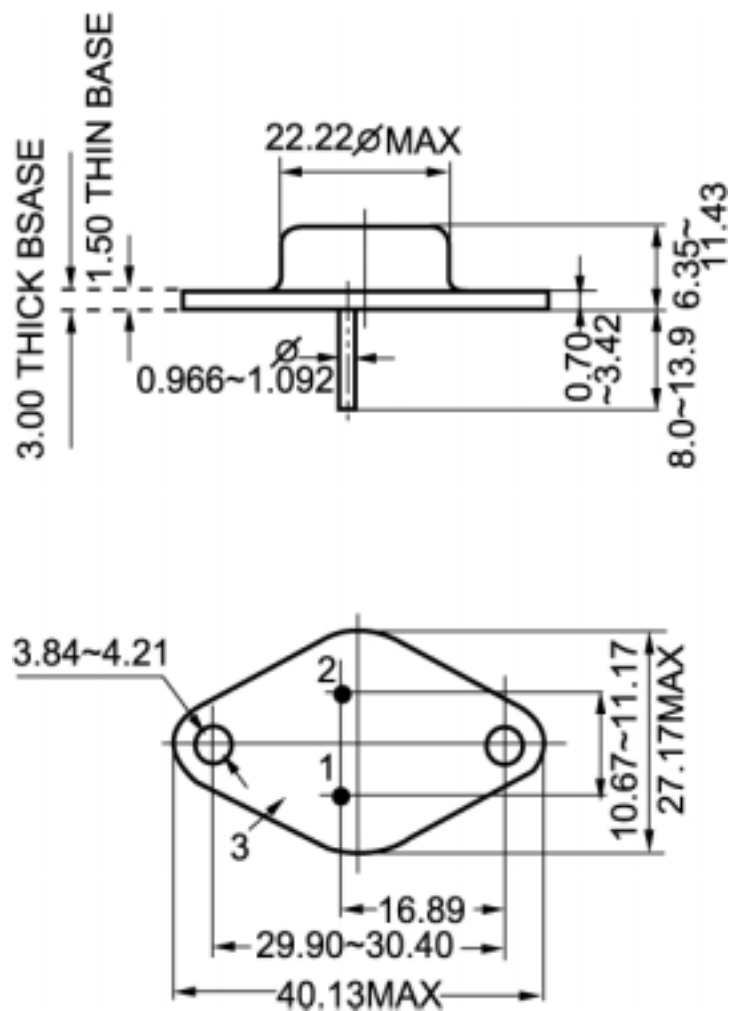


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)